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**Media Advisory**

**Innovative Silicon Z-RAM Memory Experts to Present at 2008  
IEEE International SOI Conference**

*Papers to cover new floating body memory developments and  
technology milestones*

**SANTA CLARA, Calif. — October 3, 2008** — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory technology, today announced that Dr. Mikhail Nagoga, a principal member of ISi's technical staff, and Dr. Ammar Nayfeh, a member of ISi's technical staff, will be presenting two separate papers at this year's 34<sup>th</sup> IEEE International SOI Conference on key developments in floating body memory technology. The conference will take place October 6-9, 2008 at the Mohonk Mountain House in upstate New York. More details regarding the papers are as follows:

- Dr. Ammar Nayfeh paper title: "A Leakage Current Model for SOI based Floating Body Memory that Includes the Poole-Frenkel Effect." Poster Session on Tuesday, October 7<sup>th</sup>, from 4:30 p.m. – 6:00 p.m.
- Dr. Mikhail Nagoga paper title: "Ultra-scaled Z-RAM Cell." Session 10.1 on Thursday, October 9<sup>th</sup> from 3:55p.m. – 5:25p.m.

**About the IEEE International SOI Conference**

The IEEE International SOI Conference is the premier meeting of engineers and scientists dedicated to current trends in Silicon-on-Insulator technology and provides a forum for open discussion in all areas of silicon-on-insulator technologies and their applications.



For more information, visit the conference web site at [www.soiconference.org/default.htm](http://www.soiconference.org/default.htm).

### **About Innovative Silicon**

Innovative Silicon, Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world's lowest-cost semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World Economic Forum's selection of ISi as a 2008 Technology Pioneer, and IEEE Spectrum Magazine's selection of Z-RAM as the 2007 "Emerging Technology Most Likely to Succeed." Z-RAM is a "Zero Capacitor," true single-transistor floating body memory that eliminates the complex capacitor found in today's DRAM technologies – a fundamental roadblock to Moore's Law of scaling. Z-RAM provides semiconductor manufacturers a solution for nanoscale manufacturing processes that can dramatically lower semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling \$47 million, received over 30 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D, engineering and support centers in Europe, Asia and North America. For more information see [www.z-ram.com](http://www.z-ram.com).

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